

Form PTO-1449

Document Number (Sequence)

Application Number

HT-03-025/031

10/849,310

Applicant

Cheng T. Horng et al.

Filing Date

05/19/04

Oral Exam Unit

0 INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

AUG 11 2004 (Also several sheets if necessary)

U. S. PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
6703654	3/9/04	Horng et al.	257	295	2/20/03
6614630	9/2/03	Horng et al.	360	324.12	4/23/01
6657826	12/2/03	Shimazawa et al.	360	322	8/3/01
6653704	11/25/03	Gurney et al.	257	421	9/24/02
6643104	11/4/03	Shimazawa	360	319	7/9/01
6574079	6/3/03	Sun et al.	360	324.2	7/13/01

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation
					YES NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

PD -	Y. Ando et al., "Growth mechanisms of thin insulating layer in ferromagnetic tunnel junctions prepared using various oxidation methods," J. Phys. D: Appl. Phys., Vol. 35, pp. 2415-2421.
PD -	"Exchange-biased magnetic tunnel junctions and application to nonvolatile magnetic random access memory (invited)," by S.S.P. Parkin et al., J. Appl. Phys., Vol. 85, No. 8, April 15, 1999, pp. 5828-5833.

EXAMINER

PHUC T. DANG

DATE CONSIDERED

3/10/2005

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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Doubt Number (Specimen)

HT-03-025/031

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Group Analysis

[illegible][illegible]

PD	-	"Progress and Outlook for MRAM Technology", by S. Tehrani et al., IEEE Trans. on Magnetics, Vol. 35, No. 5, Sept. 1999, pp. 2814-2819.
PD	-	"Junction area dependence of breakdown characteristics in magnetic tunnel junctions," by Kwang-Seok Kim et al., J. Appl. Phys., Vol. 93, No. 10, May 15, 2003, pp. 8364-8366.

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Doctor Number (Cpacsus)

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or over the line

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INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

U. S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

PD	-	Co-pending U.S. Patent HT-02-032, Ser.# 10/768,917, filed 01/30/04, "A Novel Oxidation Method to Fabricate Low Resistance TMR Read Head", assigned to the same assignee.
PD	-	Co-pending U.S. Patent HT-03-016, Ser.# 10/820,391, filed 04/08/04, "A Novel Oxidation Structure/Method to Fabricate a High-Performance Magnetic Tunneling Junction (MTJ), the same assigned to the same assignee."
EXAMINER		DATE CONSIDERED
PHUC T. DANG		3/10/2005

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